

# **Diode** - Power, Bare Die

# Gen VII, Fast Recovery 1200 V, 75 A

# PCFF75H120SWF

#### **Features**

- Advanced Gen VII Technology
- Fast and Soft Recovery
- Maximum Junction Temperature 175°C
- Low Forward Voltage:  $V_F = 1.78 \text{ V (Typ.)}$  @  $I_F = 75 \text{ A}$
- Easy to Parallel Operation

### **Typical Applications**

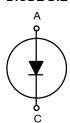
- Solar
- Energy Storage
- Industrial Motor Control

#### **MECHANICAL PARAMETERS**

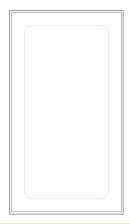
Parameter	Value	Unit	
Die Size (w/ Scribe Lane)	3,900 x 7,000	μm²	
Anode Pad Size	2,917 x 6,017	μm²	
Scribe Lane Width	80	μm	
Die Thickness	119	μm	
Top Metal	6 μm AlSiCu		
Back Metal	1.65 μm Ti/NiV/Ag		
Topside Passivation	Silicon Nitride plus Polyimide		
Wafer Diameter	200 mm		
Max Possible Die Per Wafer	910		
Recommended Storage Environment	In original container, in dry nitrogen, < 6 months at an ambient temperature of 23°C		

$$V_R = 1200 V$$
  
 $I_F = 75 A$ 

#### **DIODE DIE**



#### **DIE OUTLINE**



#### **ORDERING INFORMATION**

Device	Inking	Shipping		
PCFF75H120SWF	Yes	Sawn Wafer on Tape		

#### PCFF75H120SWF

### **ABSOLUTE MAXIMUM RATINGS** ( $T_J = 25^{\circ}C$ unless otherwise noted)

Parameter		Ratings	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	1200	V
DC Forward Current, limited by T <sub>J max</sub> (Note 1)	I <sub>F</sub>	75	Α
Pulsed Forward Current, tp limited by T <sub>J max</sub> (Note 2)	I <sub>FM</sub>	225	Α
Operating Junction Temperature	$T_J$	-40 to +175	°C
Storage Temperature Range	Tstg	+18 to +28	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Nominal forward current at  $Tc = 100^{\circ}C$  when assembled in power module
- 2. Not subject to production test verified by design/characterization.

## **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
STATIC CHARACTERISTICS (Test	ed on Wafers)	•		•	•		•
Breakdown Voltage	$V_{BR}$	I <sub>R</sub> = 1 mA		1200	-	_	V
Reverse Leakage Current	I <sub>R</sub>	V <sub>R</sub> = 1200 V		-	-	10	μΑ
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 75 A		-	1.78	2.08	V
ELECTRICAL CHARACTERISTICS	6 (Not subjected to ր	production test – verified by	design/charac	terization)			
Breakdown Voltage	$V_{BR}$	I <sub>R</sub> = 1 mA	$T_J = -40^{\circ}C$	1200	-	_	V
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 75 A	T <sub>J</sub> = 175°C	-	1.9	_	V
Reverse Recovery Time	T <sub>rr</sub>	$I_F$ = 75 A, $V_R$ = 600 V, $dI_F/dt$ = 500 A/ $\mu$ s, $T_J$ = 25°C		_	281.6	-	nS
Reverse Recovery Charge	Q <sub>rr</sub>			_	3.5	_	μC
Reverse Recovery Current	I <sub>RRM</sub>			_	24.6	_	Α
Reverse Recovery Time	T <sub>rr</sub>	$I_F = 75 \text{ A}, V_R = 600 \text{ V},$ $dI_F/dt = 500 \text{ A}/\mu\text{s}, T_J = 175^{\circ}\text{C}$		-	440.2	_	nS
Reverse Recovery Charge	Q <sub>rr</sub>			-	8.1	_	μC
Reverse Recovery Current	I <sub>RRM</sub>			_	37.0	_	Α

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTE: Switching characteristics and thermal properties are depending strongly on module design and mounting technology.

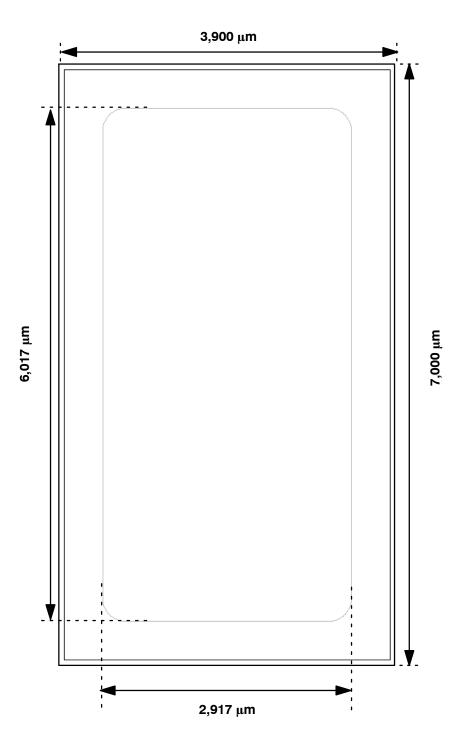


Figure 1. Die Layout

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